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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	52
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg940f128-qfn64t

3.3.2 Environmental

Table 3.3. Environmental

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{ESDHBM}	ESD (Human Body Model HBM)	T _{AMB} =25°C			1000	V
V _{ESDCDM}	ESD (Charged Device Model, CDM)	T _{AMB} =25°C			500	V

Latch-up sensitivity passed: $\pm 100 \text{ mA}/1.5 \times V_{\text{SUPPLY}}(\text{max})$ according to JEDEC JESD 78 method Class II, 85°C.

3.4 Current Consumption

Table 3.4. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash. (Production test condition = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		225	236	μA/ MHz
		48 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		225		μA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		226	238	μA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		227		μA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		228	240	μA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		229		μA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		230	243	μA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		231		μA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		232	245	μA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		233		μA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		238	250	μA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		238		μA/ MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		3.0 ¹	4.0 ¹	μA
I_{EM3}	EM3 current	$V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		0.65	1.3	μA
		$V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		2.65	4.0	μA
I_{EM4}	EM4 current	$V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		0.02	0.055	μA
		$V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		0.44	0.9	μA

¹Using backup RTC.

3.4.1 EM1 Current Consumption

Figure 3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz

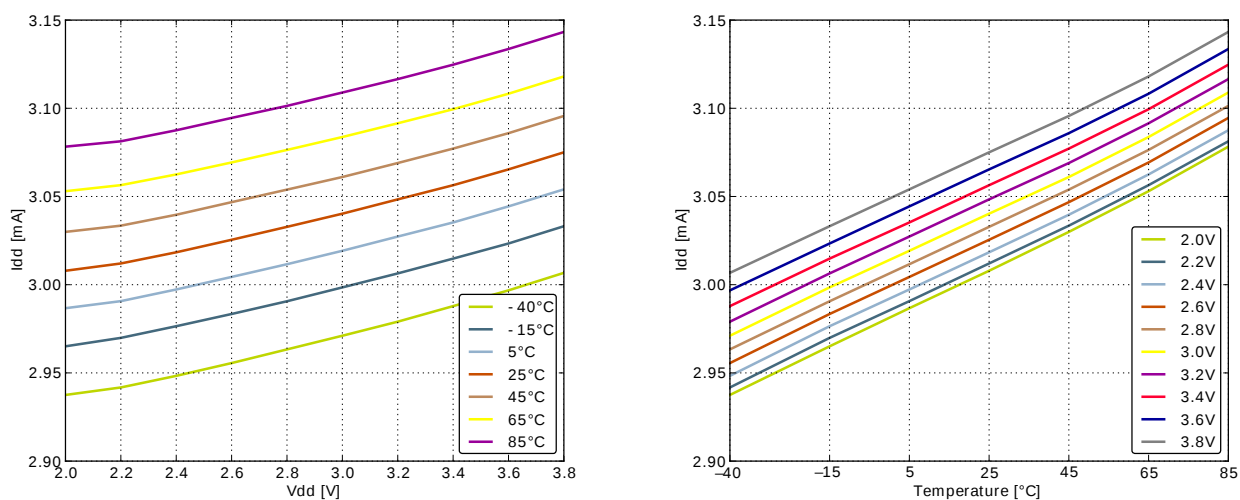


Figure 3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz

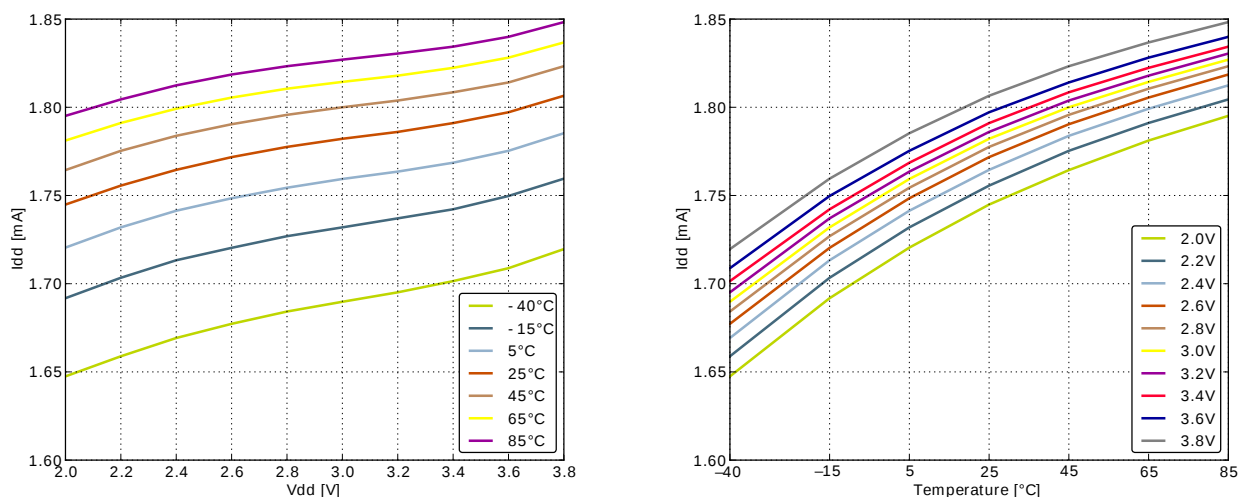


Figure 3.5. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11MHz

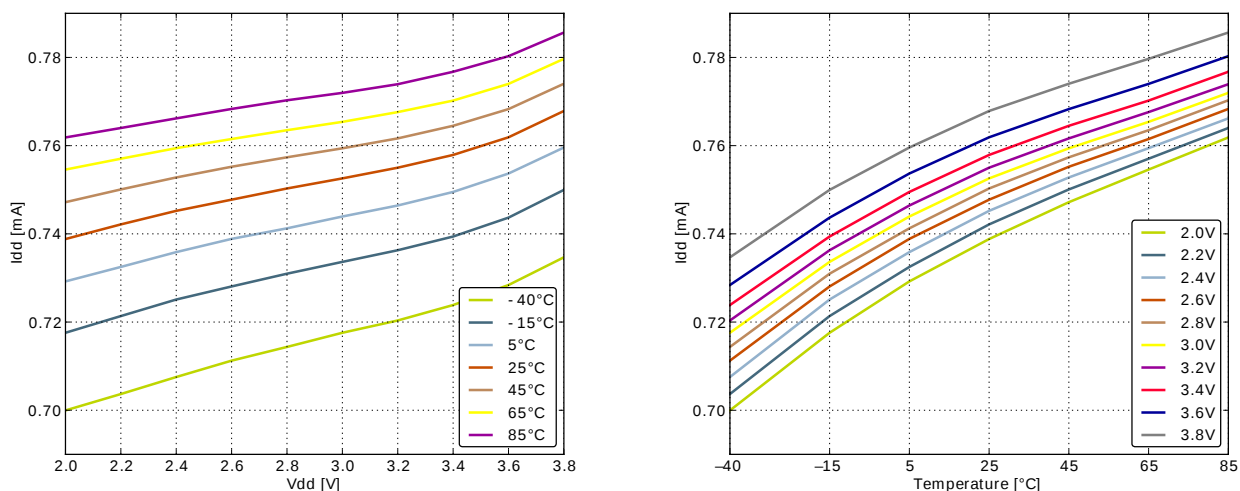
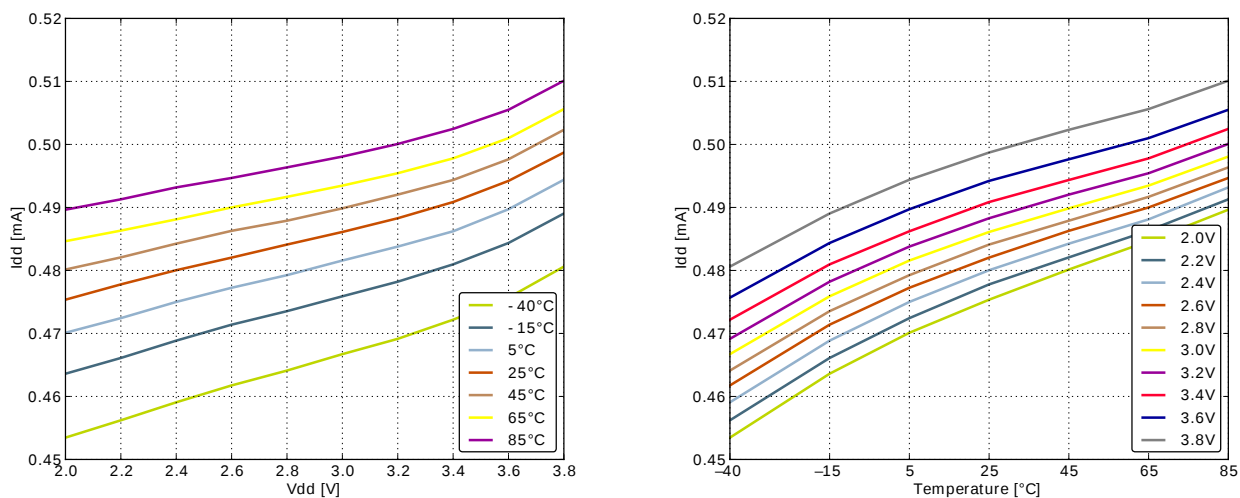


Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 6.6MHz



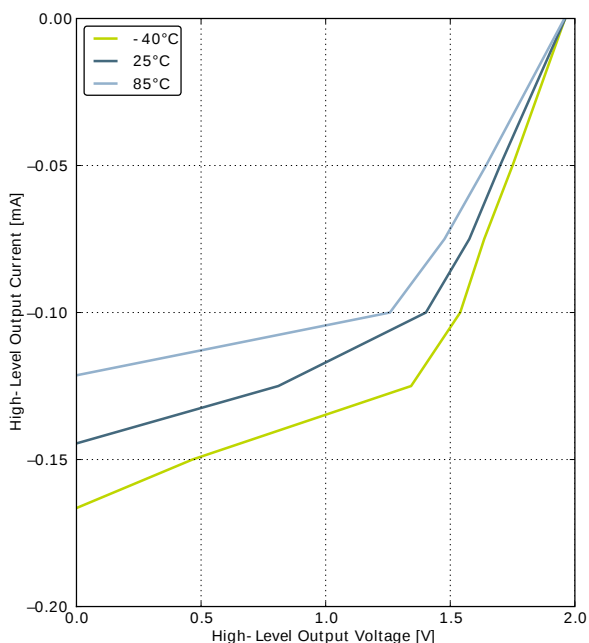
3.6 Power Management

The EFM32WG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

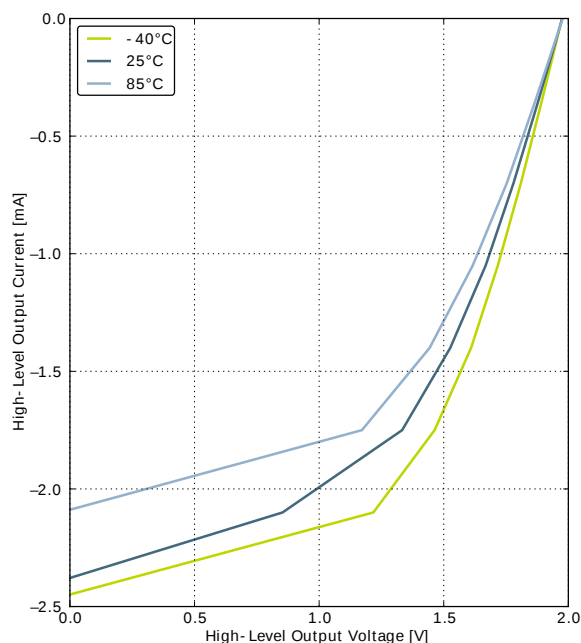
Table 3.6. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{BODextthr-}	BOD threshold on falling external supply voltage		1.74		1.96	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF
C _{USB_VREGO}	USB voltage regulator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		μF
C _{USB_VREGI}	USB voltage regulator in decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		μF

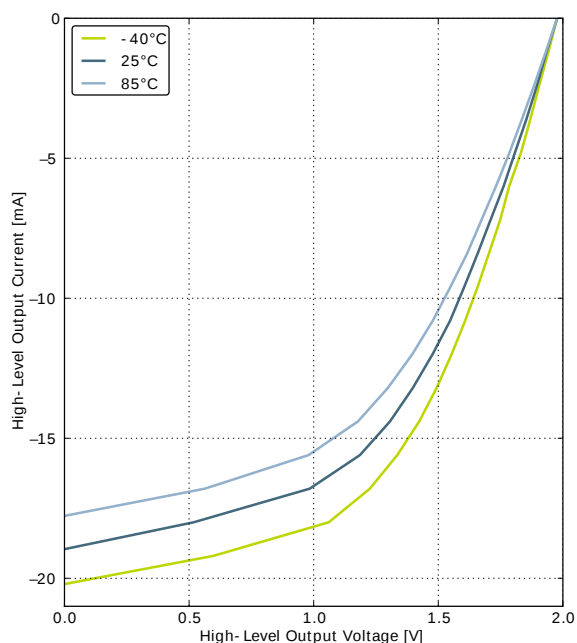
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V
		Sinking 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.25V_{DD}$	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or Vdd		± 0.1	± 100	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance $C_L=12.5-25$ pF.	$20+0.1C_L$		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance $C_L=350-600$ pF	$20+0.1C_L$		250	ns
V_{IOHYST}	I/O pin hysteresis ($V_{IOTHR+} - V_{IOTHR-}$)	$V_{DD} = 1.98 - 3.8$ V	$0.10V_{DD}$			V

Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage

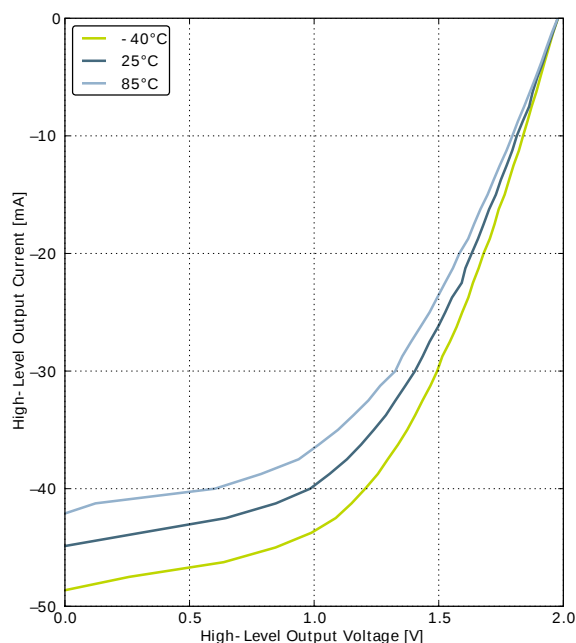
GPIO_Px_CTRL DRIVEMODE = LOWEST



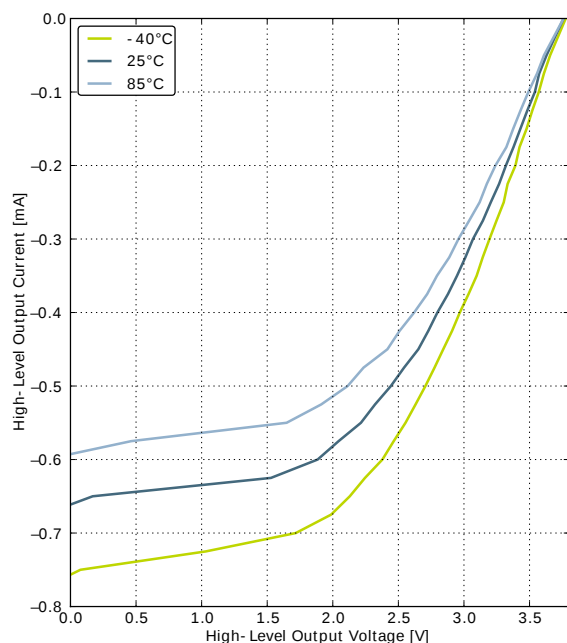
GPIO_Px_CTRL DRIVEMODE = LOW



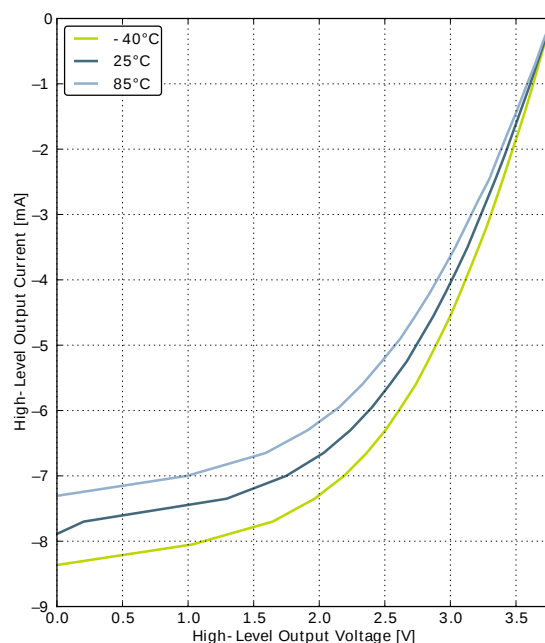
GPIO_Px_CTRL DRIVEMODE = STANDARD



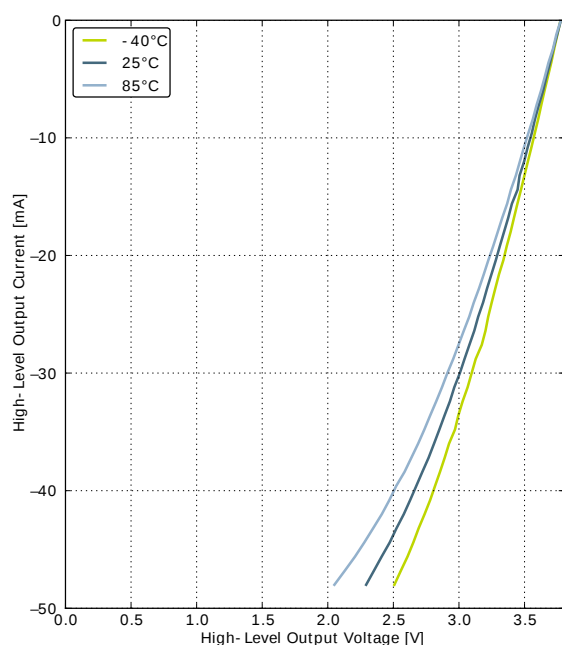
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.16. Typical High-Level Output Current, 3.8V Supply Voltage

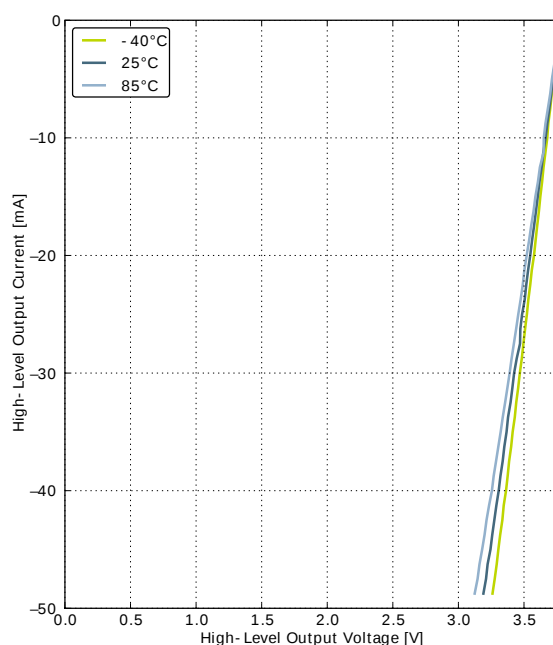
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

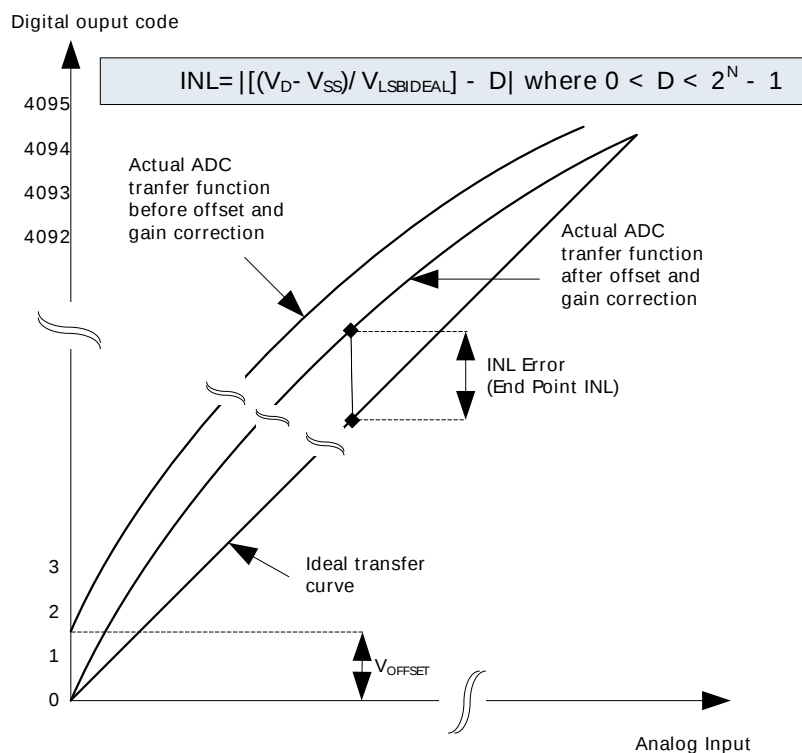
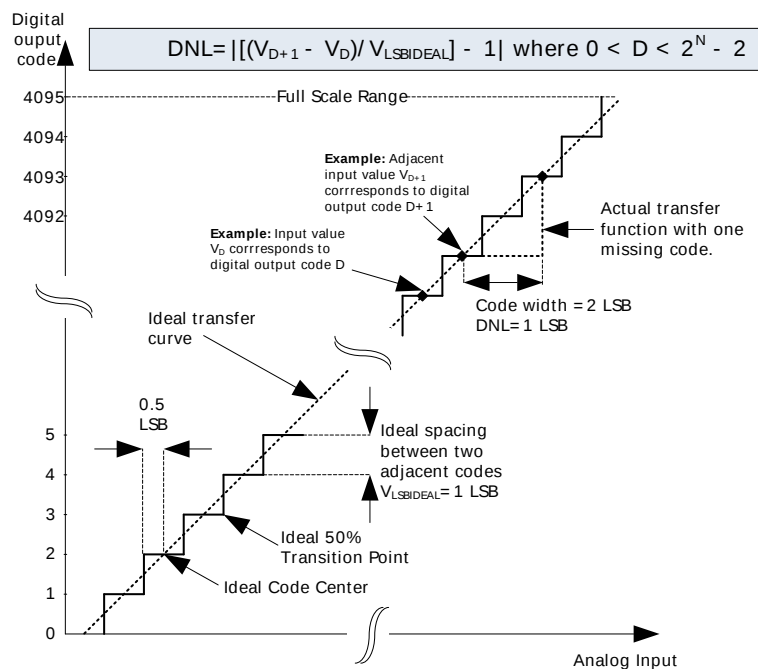


GPIO_Px_CTRL DRIVEMODE = STANDARD



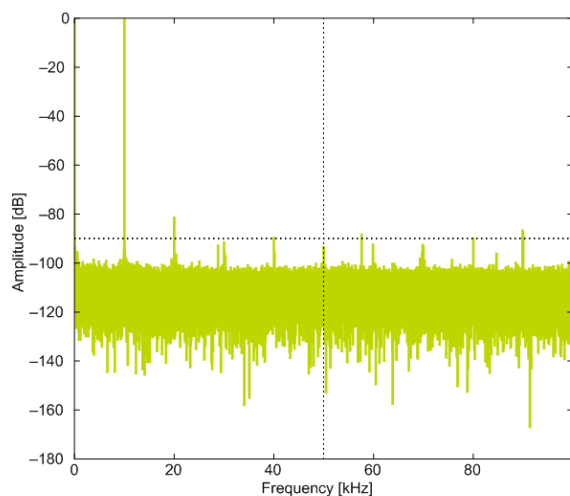
GPIO_Px_CTRL DRIVEMODE = HIGH

Symbol	Parameter	Condition	Min	Typ	Max	Unit
	and ADC core in NORMAL mode					
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V _{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differential, 2xV _{DD} reference		70		dB
SINAD _{ADC}	Signal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB

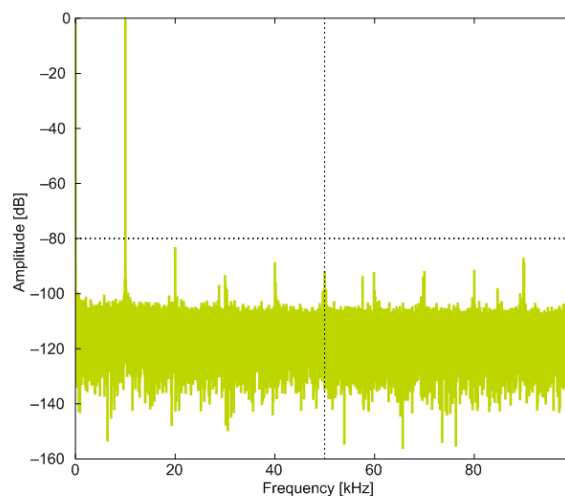
Figure 3.24. Integral Non-Linearity (INL)**Figure 3.25. Differential Non-Linearity (DNL)**

3.10.1 Typical performance

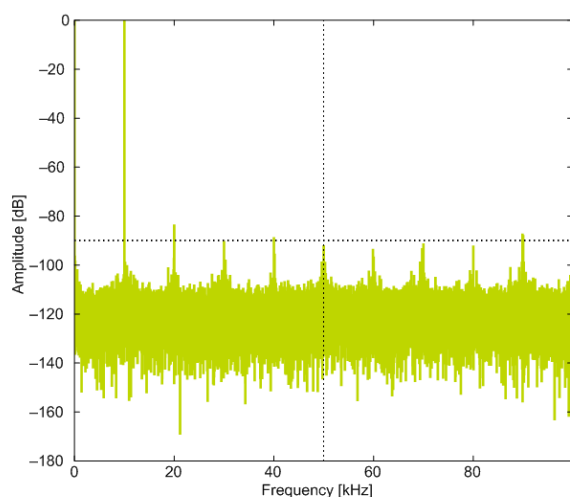
Figure 3.26. ADC Frequency Spectrum, $V_{dd} = 3V$, Temp = 25°C



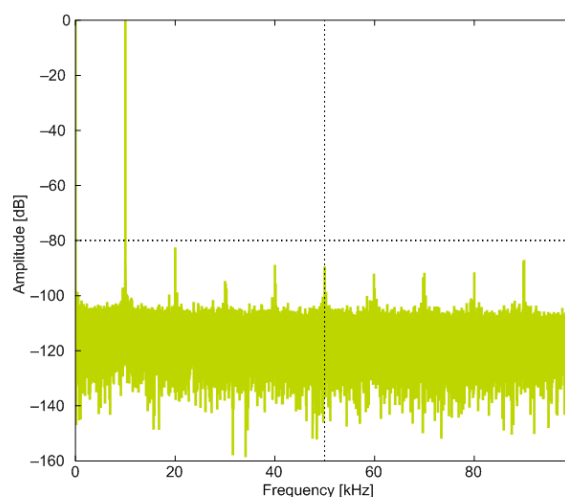
1.25V Reference



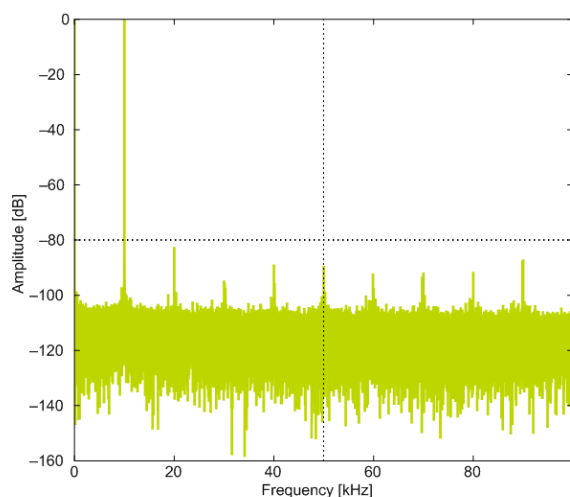
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

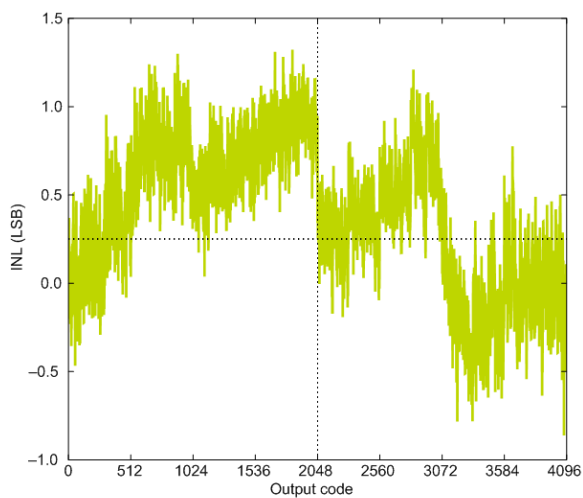
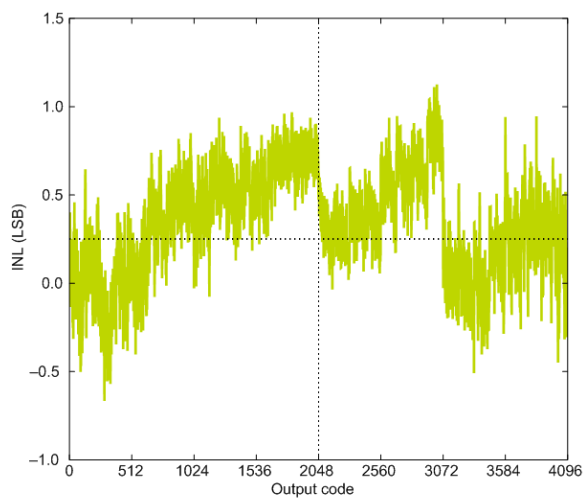
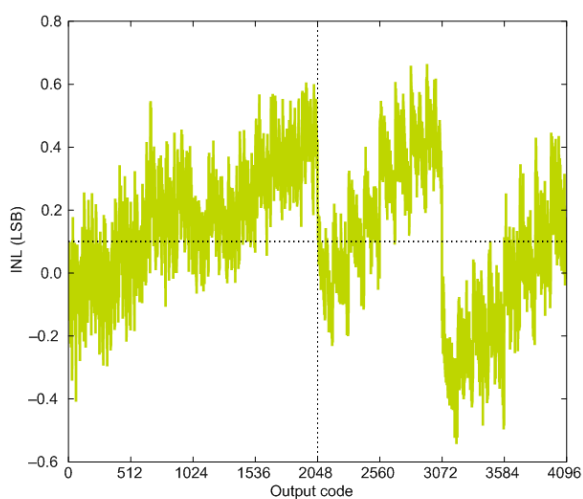
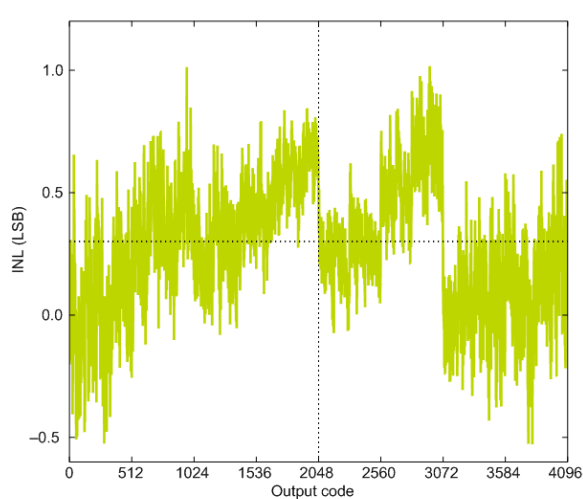
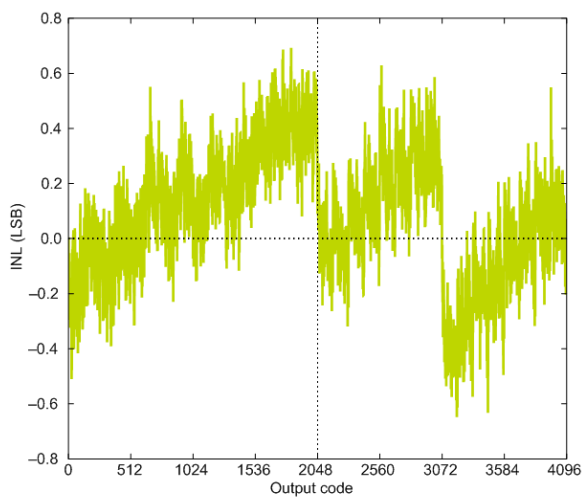
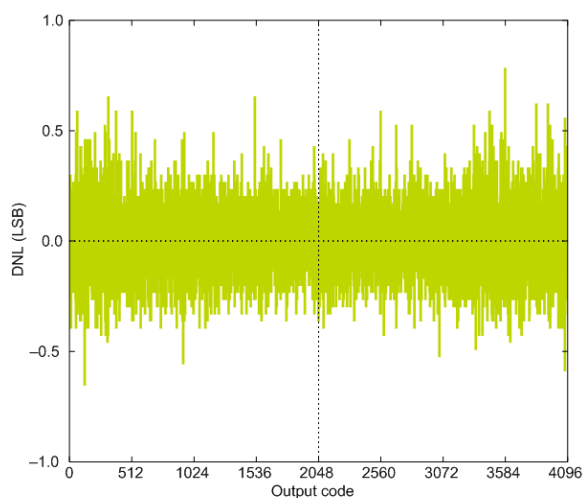
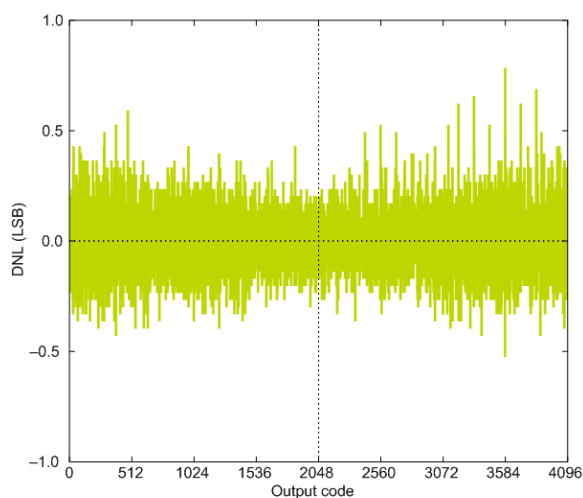
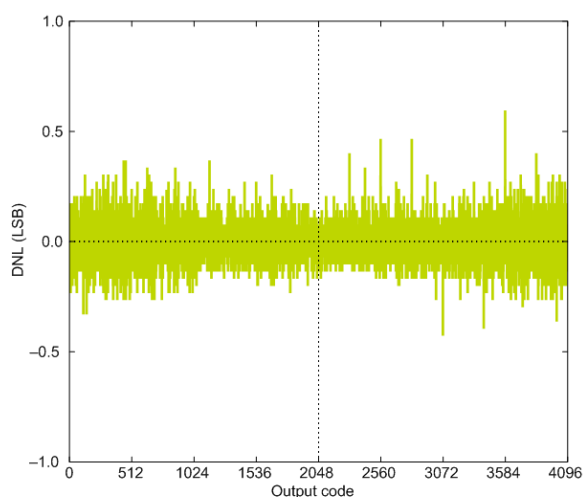
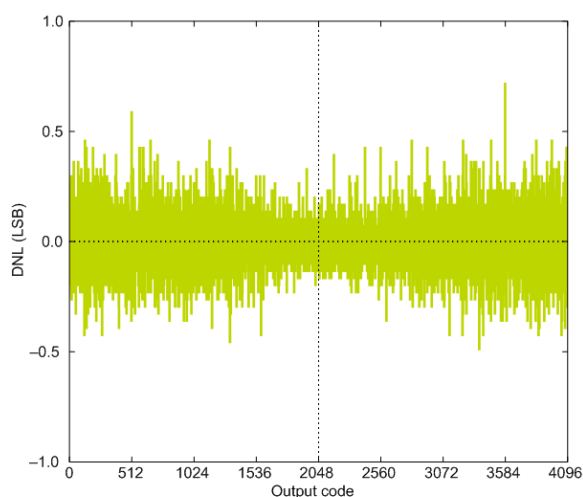
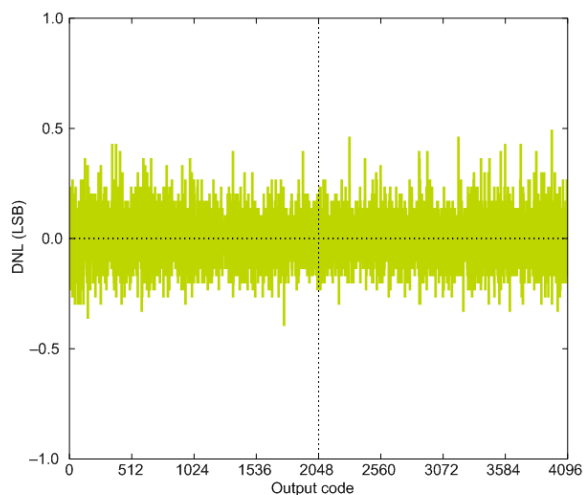
Figure 3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Figure 3.28. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
SNDR _{DAC}	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
SFDR _{DAC}	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
V _{DACOFFSET}	Offset voltage	After calibration, single ended		2	9	mV
		After calibration, differential		2		mV
DNL _{DAC}	Differential non-linearity			±1		LSB
INL _{DAC}	Integral non-linearity			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹ Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		370	460	μA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	135	μA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	μA
G _{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW _{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM _{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C _L =75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance		200			Ohm
I _{LOAD_DC}	DC Load Current				11	mA
V _{INPUT}	Input Voltage	OPAxHCMDIS=0	V _{SS}		V _{DD}	V
		OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <V _{in} <V _{DD} , OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V _{SS} <V _{in} <V _{DD} -1.2, OPAxHCMDIS=1		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR _{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/μs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/μs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/μs
N _{OPAMP}	Voltage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=0		101		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=1		141		μV _{RMS}

3.15 LCD

Table 3.20. LCD

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LCDFR}	Frame rate		30		200	Hz
NUM_{SEG}	Number of segments supported			18×8		seg
V_{LCD}	LCD supply voltage range	Internal boost circuit enabled	2.0		3.8	V
I_{LCD}	Steady state current consumption.	Display disconnected, static mode, framerate 32 Hz, all segments on.		250		nA
		Display disconnected, quadruplex mode, framerate 32 Hz, all segments on, bias mode to ONETHIRD in LCD_DISPCTRL register.		550		nA
I_{LCDBOOST}	Steady state Current contribution of internal boost.	Internal voltage boost off		0		μA
		Internal voltage boost on, boosting from 2.2 V to 3.0 V.		8.4		μA
V_{BOOST}	Boost Voltage	VBLEV of LCD_DISPCTRL register to LEVEL0		3.02		V
		VBLEV of LCD_DISPCTRL register to LEVEL1		3.15		V
		VBLEV of LCD_DISPCTRL register to LEVEL2		3.28		V
		VBLEV of LCD_DISPCTRL register to LEVEL3		3.41		V
		VBLEV of LCD_DISPCTRL register to LEVEL4		3.54		V
		VBLEV of LCD_DISPCTRL register to LEVEL5		3.67		V
		VBLEV of LCD_DISPCTRL register to LEVEL6		3.73		V
		VBLEV of LCD_DISPCTRL register to LEVEL7		3.74		V

The total LCD current is given by Equation 3.3 (p. 50) . I_{LCDBOOST} is zero if internal boost is off.

Total LCD Current Based on Operational Mode and Internal Boost

$$I_{\text{LCDTOTAL}} = I_{\text{LCD}} + I_{\text{LCDBOOST}} \quad (3.3)$$

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32WG940.

4.1 Pinout

The *EFM32WG940* pinout is shown in Figure 4.1 (p. 55) and Table 4.1 (p. 55). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32WG940 Pinout (top view, not to scale)

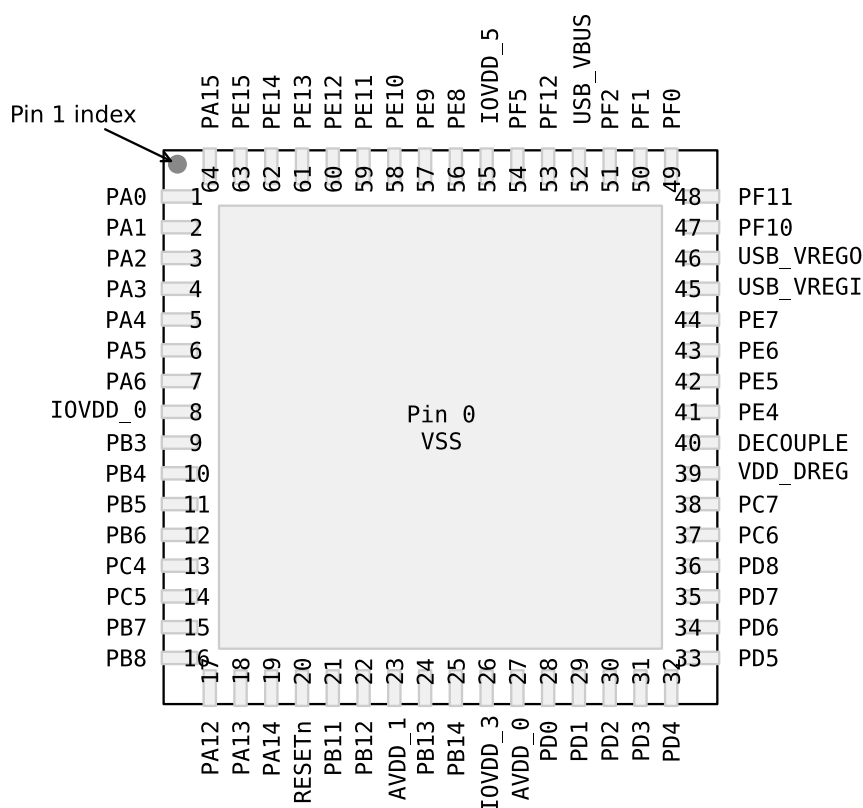


Table 4.1. Device Pinout

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
0	VSS	Ground			
1	PA0	LCD_SEG13	TIM0_CC0 #0/1/4	LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 GPIO_EM4WU0
2	PA1	LCD_SEG14	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. QFN64 PCB Land Pattern

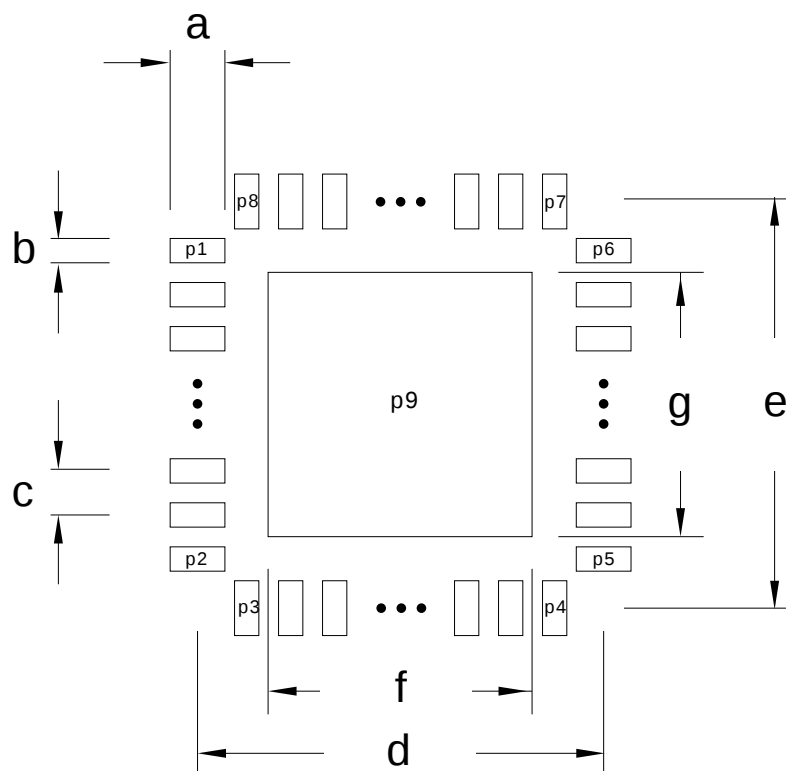
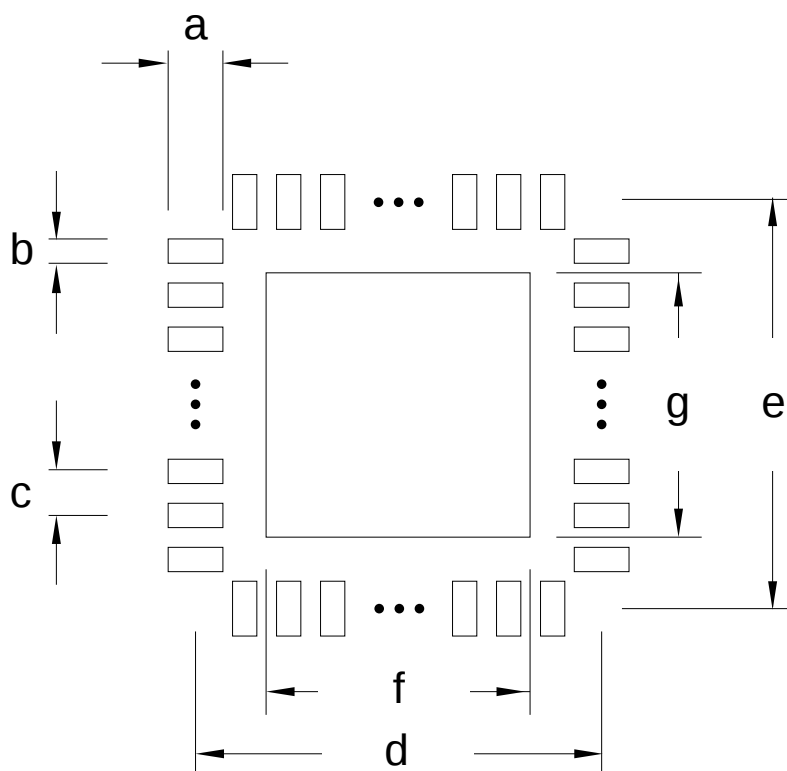
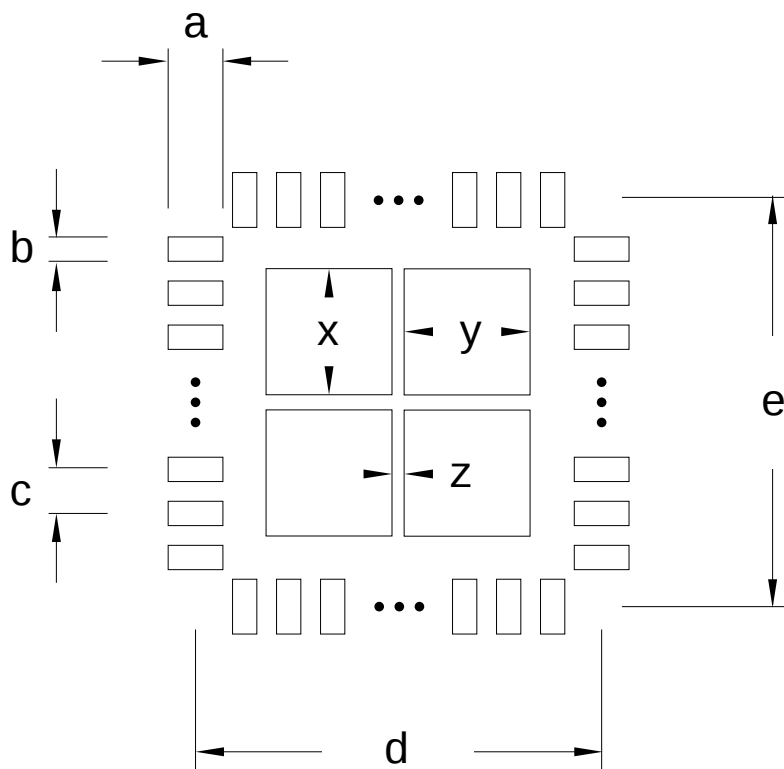


Table 5.1. QFN64 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
a	0.85	P1	1	P8	64
b	0.30	P2	16	P9	65
c	0.50	P3	17	-	-
d	8.90	P4	32	-	-
e	8.90	P5	33	-	-
f	7.20	P6	48	-	-
g	7.20	P7	49	-	-

Figure 5.2. QFN64 PCB Solder Mask**Table 5.2. QFN64 PCB Solder Mask Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.97	e	8.90
b	0.42	f	7.32
c	0.50	g	7.32
d	8.90	-	-

Figure 5.3. QFN64 PCB Stencil Design**Table 5.3. QFN64 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.75	e	8.90
b	0.22	x	2.70
c	0.50	y	2.70
d	8.90	z	0.80

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 64) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions. Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

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